

Automotive ultrafast recovery - high voltage diode

Datasheet – production data

Features

- AEC-Q101 qualified
- Ultrafast, soft recovery
- Very low conduction and switching losses
- High frequency and/or high pulsed current operation
- High reverse voltage capability
- High junction temperature

Description

The high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability like automotive applications.

These diodes also fit into auxiliary functions such as snubber, bootstrap, and demagnetization applications.

The improved performance in low leakage current, and therefore thermal runaway guard band, is an immediate competitive advantage for this device.

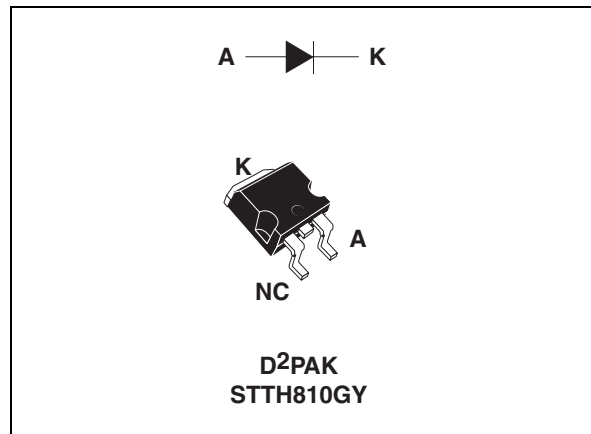


Table 1. Device summary

$I_{F(AV)}$	8 A
V_{RRM}	1000 V
T_j	175 °C
V_F (typ)	1.30 V
t_{rr} (typ)	47 ns

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1000	V
$I_{F(RMS)}$	Forward rms current		30	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 130\text{ °C}$	8	A
I_{FRM}	Repetitive peak forward current	$t_p = 5\ \mu\text{s}$, $F = 5\ \text{kHz}$ square	100	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\ \text{ms}$ sinusoidal	60	A
T_{stg}	Storage temperature range		-65 to + 175	°C
T_j	Operating junction temperature range		-40 to +175	°C

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$			5	μA
		$T_j = 125\text{ °C}$			2	20	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 8\ \text{A}$			2	V
		$T_j = 100\text{ °C}$			1.4	1.8	
		$T_j = 150\text{ °C}$			1.3	1.7	

1. Pulse test: $t_p = 5\ \text{ms}$, $\delta < 2\%$
2. Pulse test: $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.3 \times I_{F(AV)} + 0.05 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 1\text{ A}$, $di_F/dt = -50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$		64	85	ns
		$I_F = 1\text{ A}$, $di_F/dt = -100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$		47	65	
I_{RM}	Reverse recovery current	$I_F = 8\text{ A}$, $di_F/dt = -200\text{ A}/\mu\text{s}$, $V_R = 600\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$		12	16	A
S	Softness factor	$I_F = 8\text{ A}$, $di_F/dt = -200\text{ A}/\mu\text{s}$, $V_R = 600\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$		2		
t_{fr}	Forward recovery time	$I_F = 8\text{ A}$, $di_F/dt = 50\text{ A}/\mu\text{s}$ $V_{FR} = 1.5 \times V_{Fmax}$, $T_j = 25\text{ }^\circ\text{C}$			300	ns
V_{FP}	Forward recovery voltage	$I_F = 8\text{ A}$, $di_F/dt = 50\text{ A}/\mu\text{s}$, $T_j = 25\text{ }^\circ\text{C}$		5.5		V

Figure 1. Conduction losses versus average current

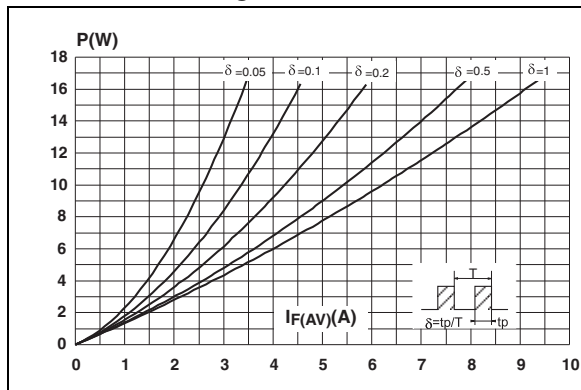


Figure 2. Forward voltage drop versus forward current

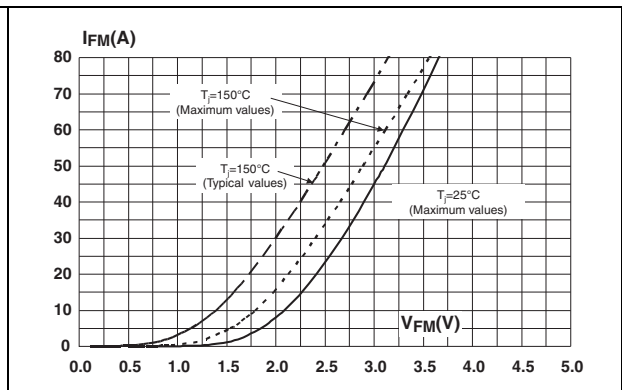


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

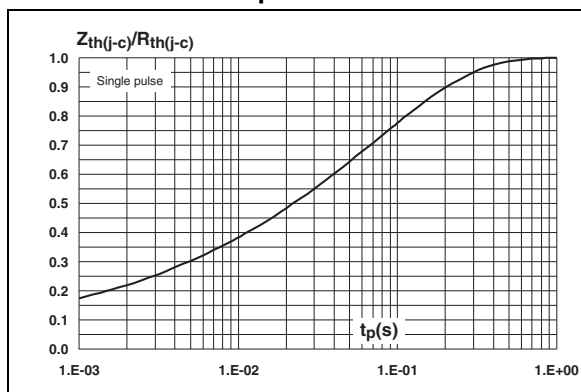


Figure 4. Peak reverse recovery current versus diF/dt (typical values)

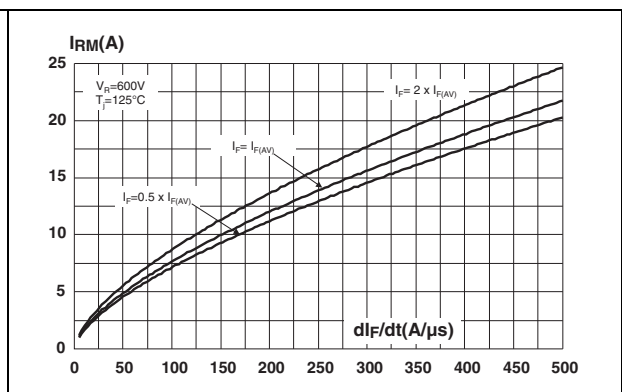


Figure 5. Reverse recovery time versus di_F/dt (typical values)

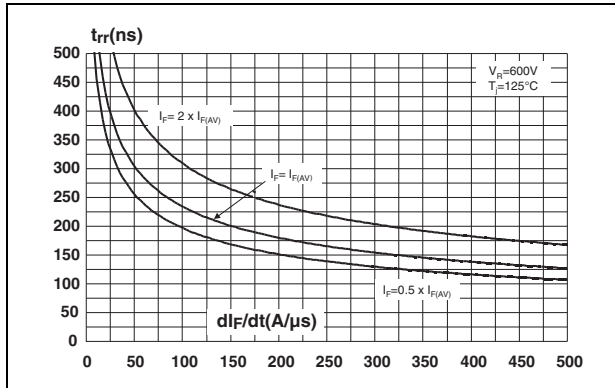


Figure 6. Reverse recovery charges versus di_F/dt (typical values)

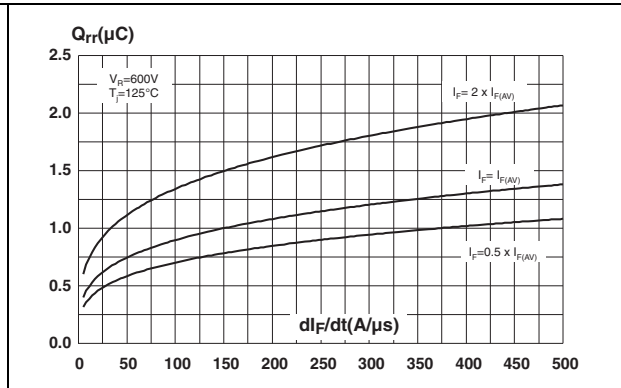


Figure 7. Softness factor versus di_F/dt (typical values)

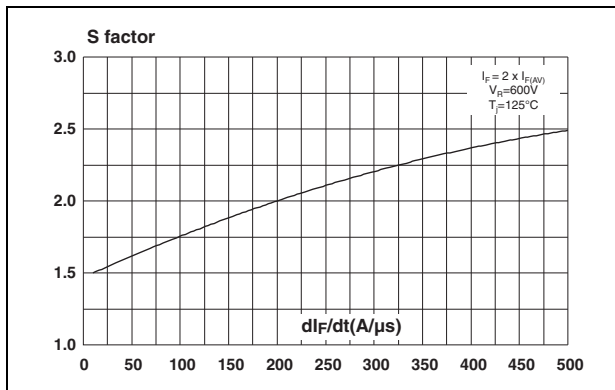


Figure 8. Relative variations of dynamic parameters versus junction temperature

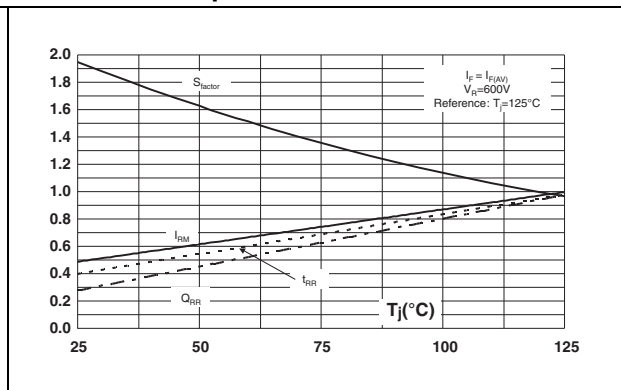


Figure 9. Transient peak forward voltage versus di_F/dt (typical values)

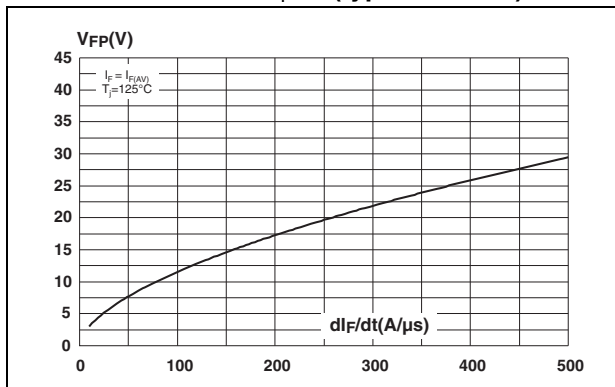


Figure 10. Forward recovery time versus di_F/dt (typical values)

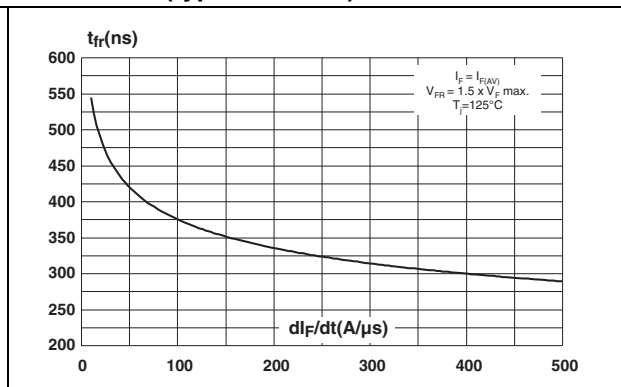


Figure 11. Junction capacitance versus reverse voltage applied (typical values)

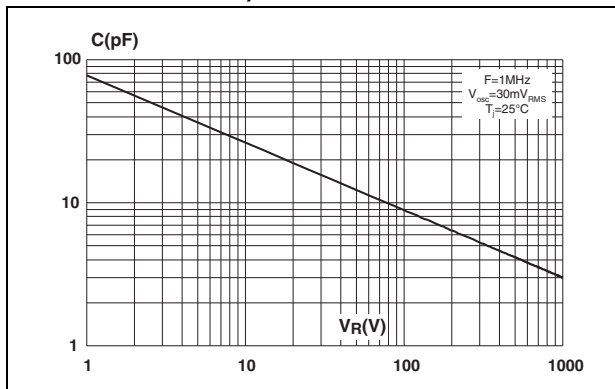
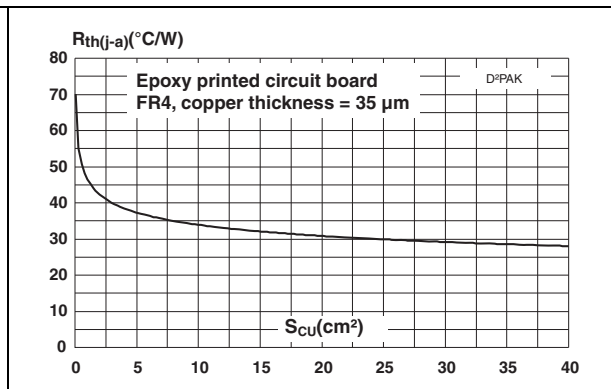


Figure 12. Thermal resistance junction to ambient versus copper surface under tab



2 Package information

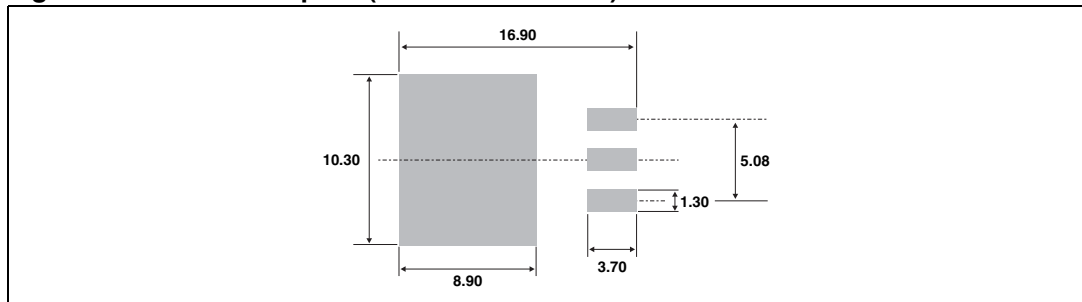
- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 6. D²PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 13. D²PAK footprint (dimensions in mm)



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH810GY-TR	STTH810GY	D ² PAK	1.48 g	1000	Tape & reel

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Oct-2012	1	First issue.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com